

EFFICIENT CLEANING BY SECONDARY IN-SITU ACTIVATION
OF ETCH PRECURSOR FROM REMOTE PLASME SOURCE
DOCKET: 6408

1/5

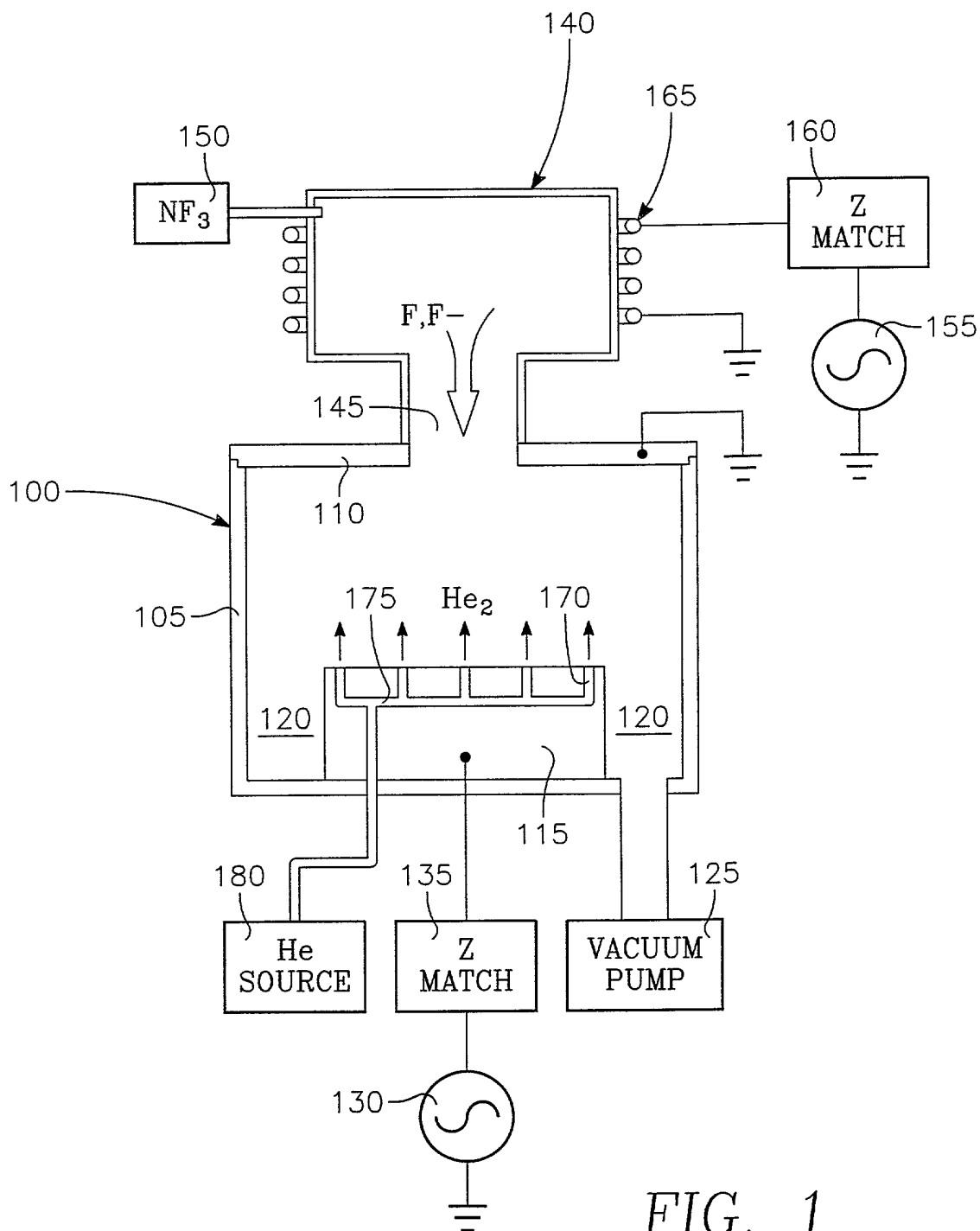


FIG. 1

EFFICIENT CLEANING BY SECONDARY IN-SITU ACTIVATION
OF ETCH PRECURSOR FROM REMOTE PLASME SOURCE
DOCKET: 6408

2/5

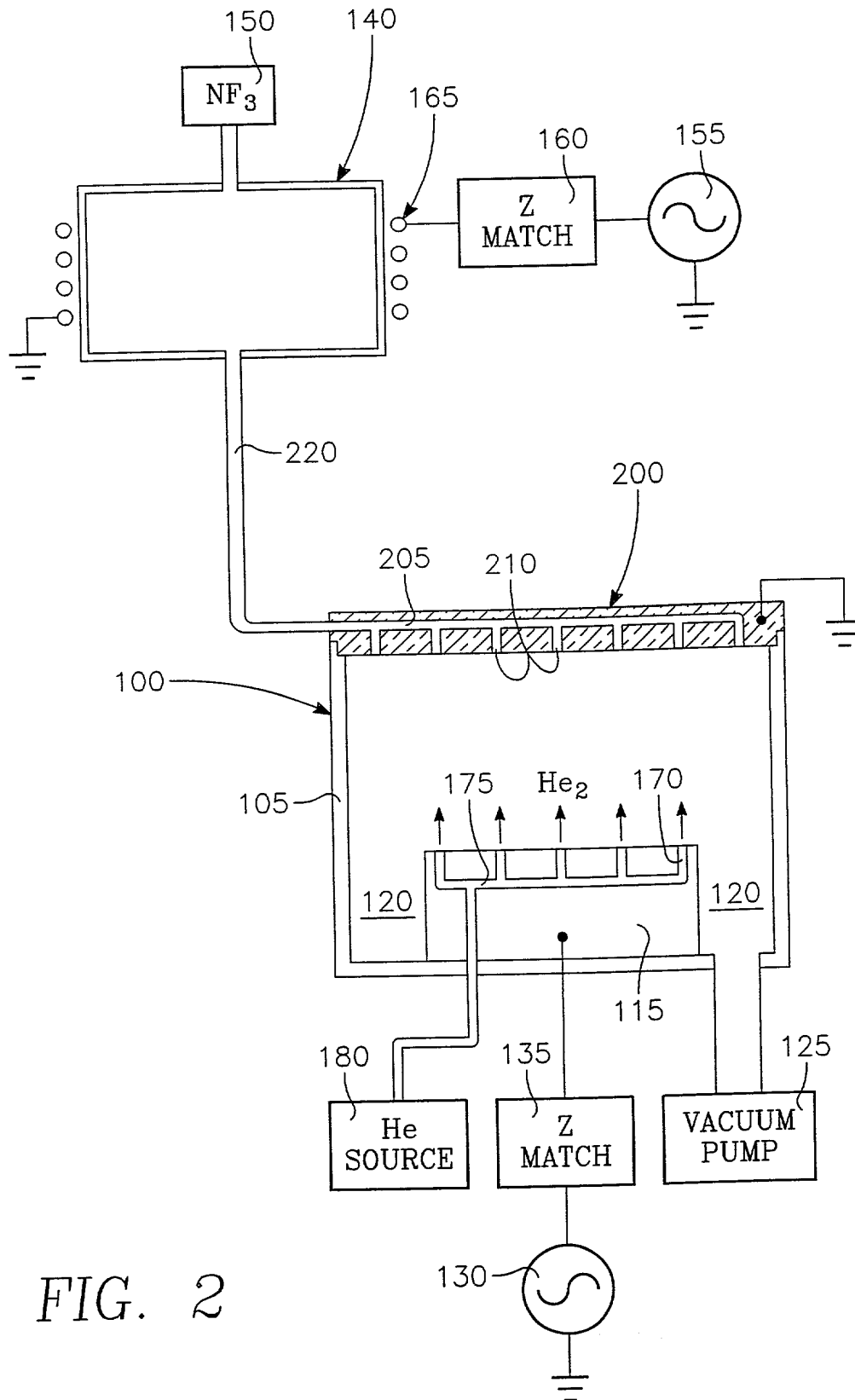


FIG. 2

EFFICIENT CLEANING BY SECONDARY IN-SITU ACTIVATION
OF ETCH PRECURSOR FROM REMOTE PLASME SOURCE
DOCKET: 6408

3/5

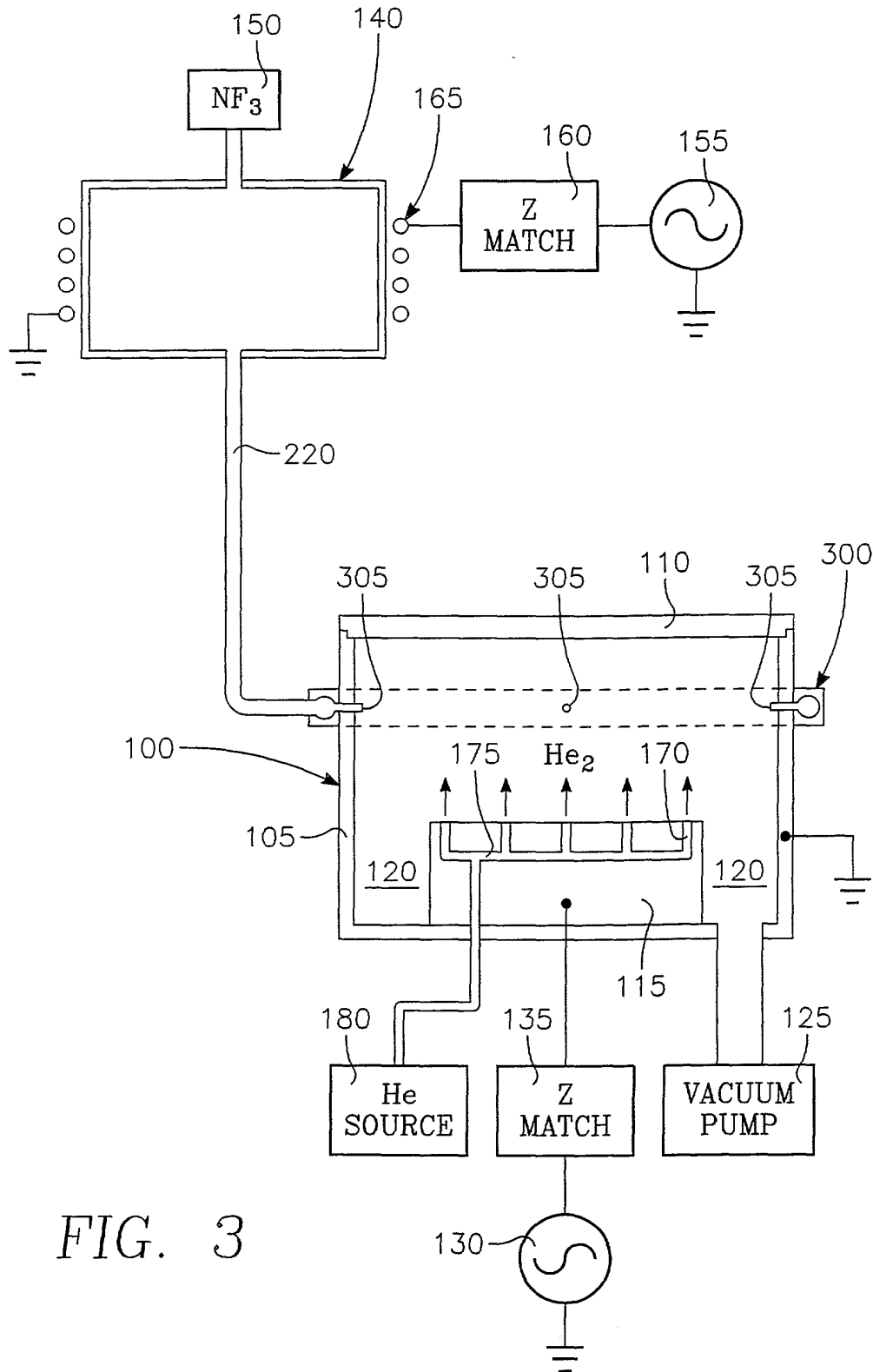


FIG. 3

EFFICIENT CLEANING BY SECONDARY IN-SITU ACTIVATION
OF ETCH PRECURSOR FROM REMOTE PLASMA SOURCE
DOCKET: 6408

4/5

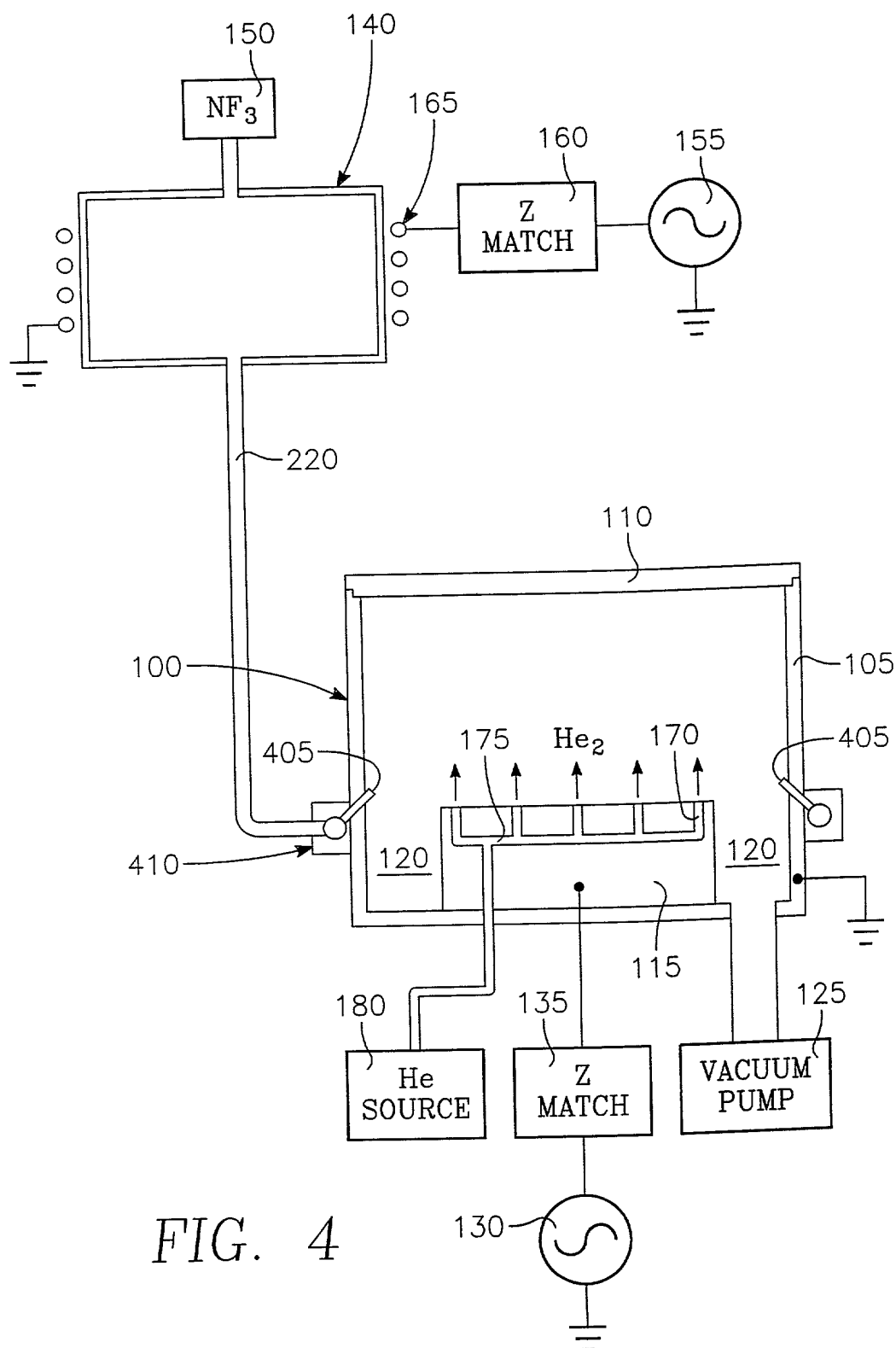


FIG. 4

EFFICIENT CLEANING BY SECONDARY IN-SITU ACTIVATION
OF ETCH PRECURSOR FROM REMOTE PLASMA SOURCE
DOCKET: 6408

5/5

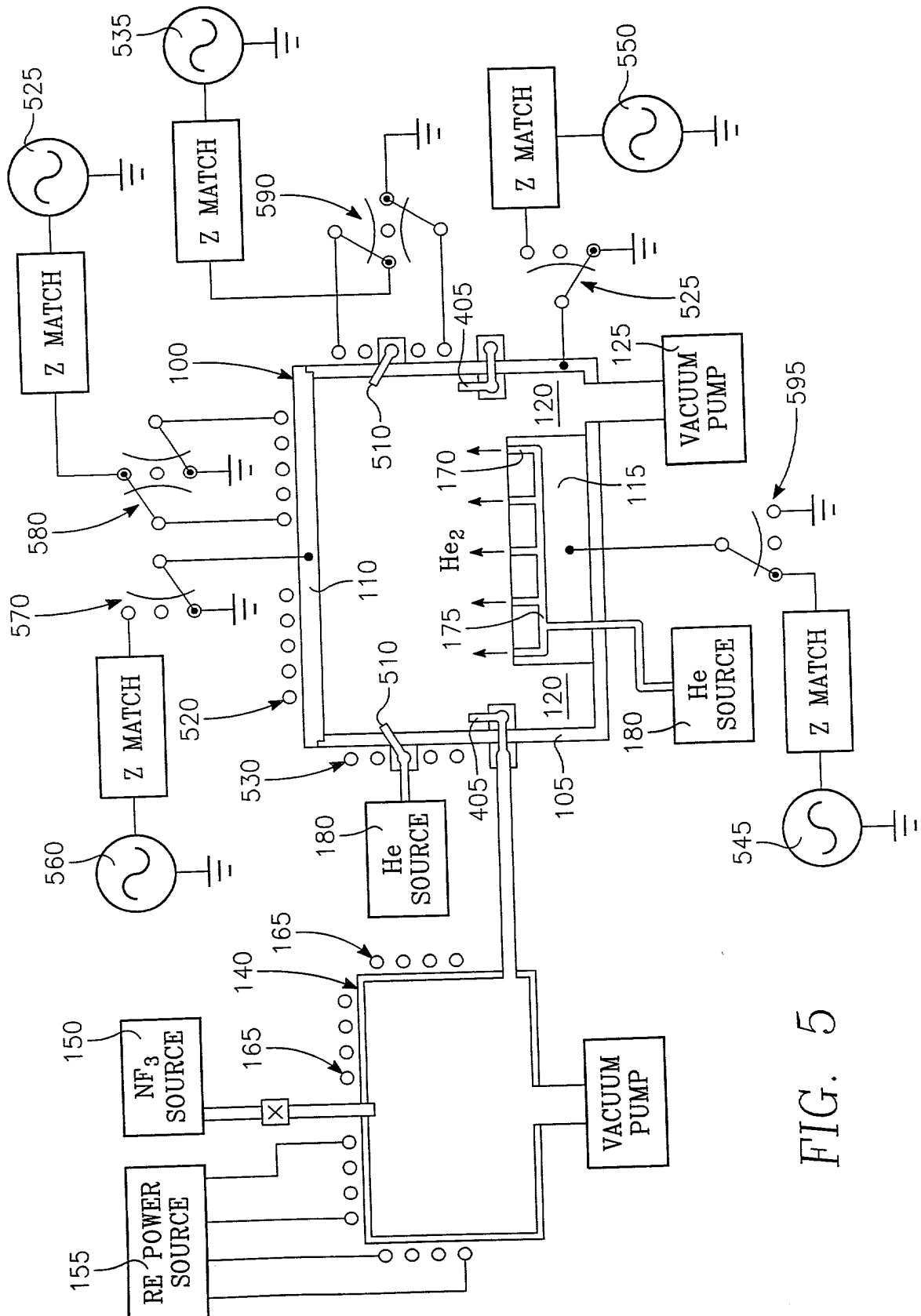


FIG. 5

202070" SECRET